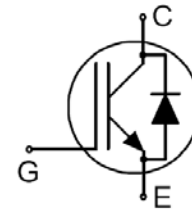


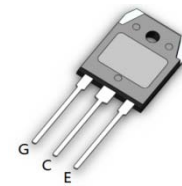
### 1350V , 25A , Trench-FS IGBT

#### Features

- Advanced Trench+FS (Field Stop) IGBT technology
- Low Collector-Emitter Saturation voltage, typical data is 1.9V @ 25A.
- Easy parallel switching capability due to positive Temperature coefficient in Vce.
- 10uS short-circuit
- Fast switching
- High input impedance
- Pb- Free product



Schematic Diagram



TO3PN

#### Applications

- Power switch circuit of induction cooker.

#### Electrical characteristics(T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test conditions	Units	Min.	Typ.	Max.
V <sub>(BR)CES</sub>	Collector - Emitter breakdown voltage	V <sub>GE</sub> = 0V, I <sub>D</sub> = 0.5mA	V	1350	—	—
V <sub>CE(sat)</sub>	Collector-Emitter Saturation voltage	V <sub>GE</sub> =15V, I <sub>C</sub> =25A,T <sub>C</sub> =25°C	V	—	1.9	2.1
		V <sub>GE</sub> =15V, I <sub>C</sub> =25A,T <sub>C</sub> =125°C	V	—	2.05	—
V <sub>GE(th)</sub>	Gate threshold voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>D</sub> = 0.4mA	V	4.0	5.2	6.5
V <sub>F</sub>	Diode Forward voltage	I <sub>C</sub> =25A	V	—	2.5	2.9
I <sub>GES</sub>	Gate to Emitter Forward Leakage	V <sub>ge</sub> =+30V	nA	—	—	200
I <sub>GESR</sub>	Gate to Emitter reverse Leakage	V <sub>ge</sub> =-30V		-200	—	—
I <sub>CES</sub>	Zero gate voltage collector current	V <sub>CE</sub> =1350V	uA	—	—	100